Thyristor Module

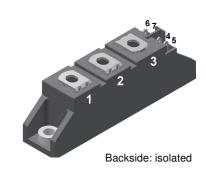
MCC44-18io1B

V_{RRM}	<i>=</i> 2x 1800 V		
I _{tav}	=	49 A	
VT	=	1.34 V	

Phase leg

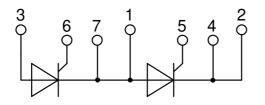
Part number

MCC44-18io1B





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Features / Advantages:

- Thyristor for line frequency
- Planar passivated chip
- Long-term stability
- Direct Copper Bonded Al2O3-ceramic

Applications:

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

Package: TO-240AA

- Isolation Voltage: 3600 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

Terms and Conditions of Usage

The data contained in this product data sheet is exclusively intended for technically trained staff. The user will have to evaluate the suitability of the product for the intended application and the completeness of the product data with respect to his application. The specifications of our components may not be considered as an assurance of component characteristics. The information in the valid application- and assembly notes must be considered. Should you require product information in excess of the data given in this product data sheet or which concerns the specific application of your product, please contact your local sales office. Due to technical requirements our product may contain dangerous substances. For information on the types in question please contact your local sales office. Should you intend to use the product in aviation, in health or life endangering or life support applications, please notify. For any such application we urgently recommend

to perform joint risk and quality assessments;
the conclusion of quality agreements;

- to establish joint measures of an ongoing product survey, and that we may make delivery dependent on the realization of any such measures.

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Data according to IEC 60747and per semiconductor unless otherwise specified

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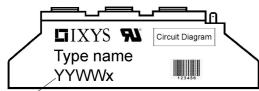
MCC44-18io1B

Thyristo				1	Ratings		
Symbol	Definition	Conditions		min.	typ.	max.	Uni
V _{RSM/DSM}	max. non-repetitive reverse/forwa	rd blocking voltage	$T_{vJ} = 25^{\circ}C$			1900	\ \
V _{RRM/DRM}	max. repetitive reverse/forward bl		$T_{VJ} = 25^{\circ}C$			1800	١
R/D	reverse current, drain current	V _{R/D} = 1800 V	$T_{vJ} = 25^{\circ}C$			100	μ/
		V _{R/D} = 1800 V	$T_{vJ} = 125^{\circ}C$			5	m/
V _T	forward voltage drop	$I_{T} = 100 \text{ A}$	$T_{vJ} = 25^{\circ}C$			1.34	١
		$I_{T} = 200 \text{ A}$				1.75	١
		$I_{T} = 100 \text{ A}$	$T_{VJ} = 125 \degree C$			1.34	١
		I _T = 200 A				1.80	١
ITAV	average forward current	$T_c = 85^{\circ}C$	T _{vJ} = 125°C			49	ŀ
I _{T(RMS)}	RMS forward current	180° sine				77	ļ
V _{T0}	threshold voltage		T _{vJ} = 125°C			0.85	١
r _T	slope resistance } for power lo	oss calculation only				5.3	m۵
R _{thJC}	thermal resistance junction to cas	e				0.53	K/W
R _{thCH}	thermal resistance case to heatsi				0.20		K/W
P _{tot}	total power dissipation		$T_c = 25^{\circ}C$			180	W
I _{TSM}	max. forward surge current	t = 10 ms; (50 Hz), sine	$T_{v,i} = 45^{\circ}C$			1.15	k/
•15M		t = 8,3 ms; (60 Hz), sine	$V_{\rm R} = 0 V$			1.24	k/
		t = 0,0 ms; (50 Hz), sine t = 10 ms; (50 Hz), sine	$T_{\rm WI} = 125^{\circ}{\rm C}$			980	
		t = 8,3 ms; (60 Hz), sine	$V_{\rm NR} = 0 V$			1.06	, k/
l²t	value for fusing	t = 0.5 ms; (50 Hz), sine	$\frac{v_{R} = 0.7}{T_{V,I} = 45^{\circ}C}$			6.62	
	value for fusing						ł
		t = 8,3 ms; (60 Hz), sine t = 10 ms; (50 Hz), sine	$\frac{V_{R} = 0 V}{T_{R} + 105 \circ C}$			6.40	<u> </u>
			$T_{VJ} = 125^{\circ}C$			4.80	kA ² s
		t = 8,3 ms; (60 Hz), sine	$V_{\rm R} = 0 V$		F 4	4.63	
C,	junction capacitance	$V_{\rm R} = 400 \text{V} \text{f} = 1 \text{MHz}$	$T_{VJ} = 25^{\circ}C$		54	10	pl
P _{GM}	max. gate power dissipation	t _P = 30 μs	$T_c = 125^{\circ}C$			10	W
		$t_{P} = 300 \mu s$				5	W
P _{GAV}	average gate power dissipation					0.5	N
(di/dt) _{cr}	critical rate of rise of current	$T_{v_J} = 125 ^{\circ}C; f = 50 Hz$ re	• • •			150	A/μ
		t_{P} = 200 µs; di _G /dt = 0.45 A/µs; -					
		$I_{g} = 0.45 \text{ A}; \text{ V} = \frac{2}{3} \text{ V}_{\text{DRM}}$ no	on-repet., $I_{T} = 49 \text{ A}$			500	A/μ
(dv/dt) _{cr}	critical rate of rise of voltage	$V = \frac{2}{3} V_{DRM}$	$T_{vJ} = 125^{\circ}C$			1000	V/μ
		$R_{GK} = \infty$; method 1 (linear volta	ge rise)				1 1 1 1
V _{gt}	gate trigger voltage	$V_{D} = 6 V$	$T_{vJ} = 25^{\circ}C$			1.5	١
			$T_{vJ} = -40 ^{\circ}C$			1.6	١
I _{GT}	gate trigger current	$V_{D} = 6 V$	$T_{vJ} = 25^{\circ}C$			100	m/
			$T_{vJ} = -40^{\circ}C$			200	mA
V _{gd}	gate non-trigger voltage	$V_{D} = \frac{2}{3} V_{DBM}$	T _{vJ} = 125°C			0.2	١
I _{GD}	gate non-trigger current					10	m/
	latching current	t _p = 10 μs	T _{vJ} = 25°C			450	m/
•L	Ŭ	$I_{g} = 0.45 \text{ A}; \text{ di}_{g}/\text{dt} = 0.45 \text{ A}/\mu\text{s}$					
I _H	holding current	$V_{\rm D} = 6 V R_{\rm GK} = \infty$	T _{vJ} = 25°C			200	m/
	gate controlled delay time	$V_{\rm D} = \frac{1}{2} V_{\rm DRM}$	$T_{VJ} = 25 ^{\circ}\text{C}$			200	1
t _{gd}	gate controlled delay lille					2	μ
	turn-off time	$I_{\rm G} = 0.45 \text{A}; \text{di}_{\rm G}/\text{dt} = 0.45 \text{A}/\mu\text{s}$			450		
t _q	lui 1-011 lii 110	$V_{R} = 100 \text{ V}; I_{T} = 120 \text{ A}; \text{ V} = \frac{2}{3}$	$3 V_{\text{DRM}} = 100 \text{°C}$	1	150		μ

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Package	TO-240AA				F	Rating	S	
Symbol	Definition	Conditions			min.	typ.	max.	Unit
I _{RMS}	RMS current	per terminal					200	Α
\mathbf{T}_{v_J}	virtual junction temperature				-40		125	°C
T _{op}	operation temperature				-40		100	°C
T _{stg}	storage temperature				-40		125	°C
Weight						81		g
M _D	mounting torque		2.5		4	Nm		
M _T	terminal torque				2.5		4	Nm
d _{Spp/App}	oroopaga distance on surfac	o / striking distance through air	terminal to terminal	13.0	9.7			mm
d _{Spb/Apb}	creepage distance on surface striking distance through air		terminal to backside	16.0	16.0			mm
V	isolation voltage	t = 1 second			3600			V
	t = 1 minute		50/60 Hz, RMS; lıso∟ ≤ 1 mA		3000			V



Date Code

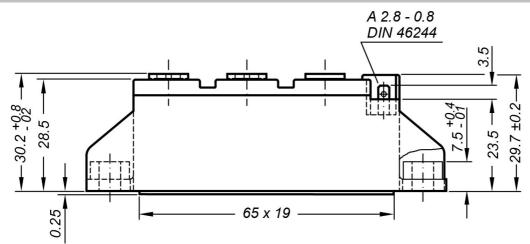
Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MCC44-18io1B	MCC44-18io1B	Box	36	454524

Equivalent Circuits for Simulation		* on die level	T _{vj} = 125 °C	
$I \rightarrow V_0$)- <u> </u>	Thyristor		
V _{0 max}	threshold voltage	0.85		V
$\mathbf{R}_{0 \max}$	slope resistance *	4.1		mΩ

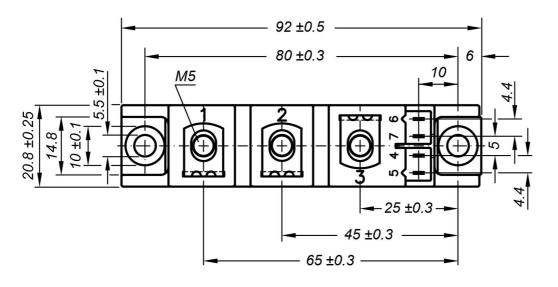
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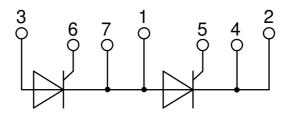
Outlines TO-240AA



General tolerance: DIN ISO 2768 class "c"



Optional accessories: Keyed gate/cathode twin plugs Wire length: 350 mm, gate = white, cathode = red UL 758, style 3751 Type **ZY 200L** (L = Left for pin pair 4/5) Type **ZY 200R** (R = Right for pin pair 6/7)



sin

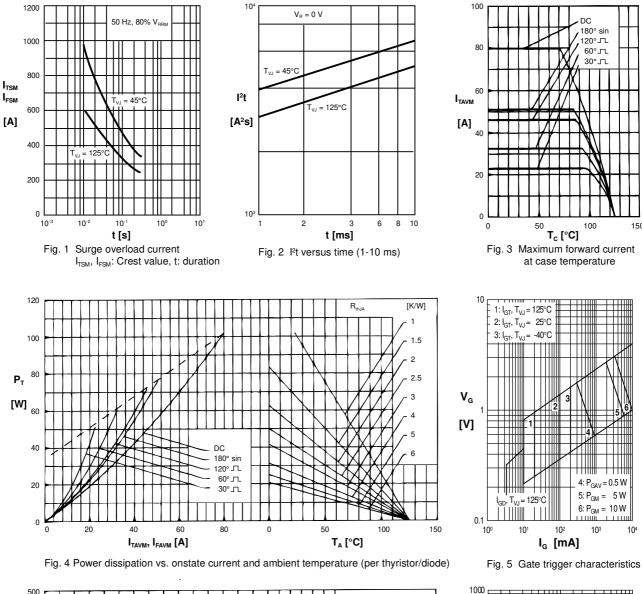
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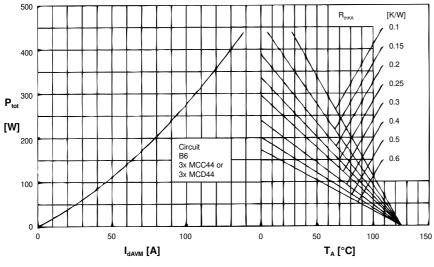
= 0.5 W

1.1.111

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Thyristor





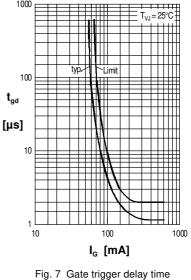
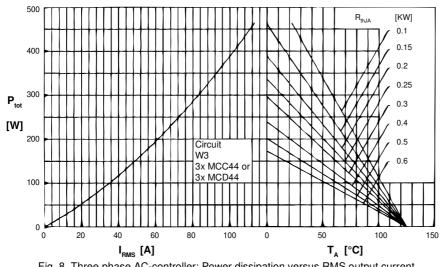


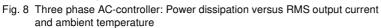
Fig. 6 Three phase rectifier bridge: Power dissipation versus direct output current and ambient temperature

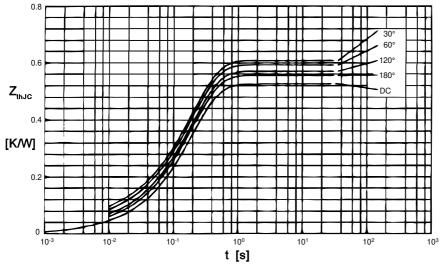
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Thyristor



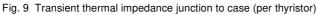


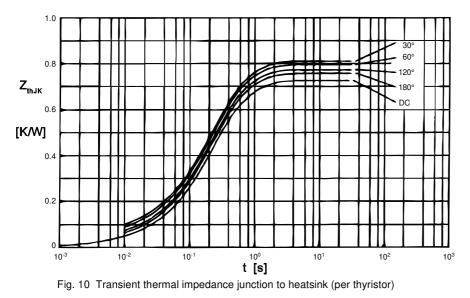


1100		
d	R _{thJC} [K/W]	
DC	0.53	
180°	0.55	
120°	0.58	
60°	0.60	
30°	0.62	
Constants	s for Z _{thJC} calculation:	:
i R _{thi} [K/	/W] t _i [s]	
1 0.01	5 0.0035	

 $\mathbf{R}_{_{thJC}}$ for various conduction angles d:

I	0.015	0.0035
2	0.026	0.0200
3	0.489	0.1950





$R_{_{thJK}}$ for various conduction angles d:				
	d R _u	_{лэк} [K/W]		
	DC	0.73		
	180°	0.75		
	120°	0.78		
	60°	0.80		
	30°	0.82		
Co	nstants fo	r Z _{thJK} calculation:		
i	R _{thi} [K/W] t _i [s]		
1	0.015	0.0035		
2	0.026	0.0200		
3	0.489	0.0195		
4	0.200	0.6800		

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